This product complies with the RoHS Directive (EU 2002/95/EC).

UP05C8PG

Silicon NPN epitaxial planar type (Tr)
Silicon epitaxial planar type (CCD load device)

For CCD output circuits

■ Features

- Two elements incorporated into one package (Tr + CCD load device)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

■ Basic Part Number

- 2SC3932G + CCD load device

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Tr	Collector-base voltage (Emitter open)	V_{CBO}	30	V
	Collector-emitter voltage (Base open)	V_{CEO}	20	V
	Emitter-base voltage (Collector open)	V_{EBO}	3	V
	Collector current	I_C	50	mA
CCD load device	Limiting element voltage	V_{max}	40	V
	Limiting element current	I_{max}	10	mA
Overall	Total power dissipation *	P_T	125	mW
	Junction temperature	T_j	125	°C
	Storage temperature	T_{stg}	–55 to +125	°C

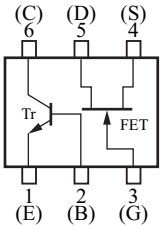
Note) * : Measuring on substrate at 17 mm × 10 mm × 1 mm

■ Package

- Code
  SSMini6-F2
- Pin Name
  1: Emitter 4: Source
  2: Base 5: Drain
  3: Gate 6: Collector

■ Marking Symbol: 4X

■ Internal Connection



■ Electrical Characteristics $T_a = 25°C \pm 3°C$

• Tr

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100\ \mu A$, $I_E = 0$	30			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu A$, $I_C = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{CE} = 10$ V, $I_C = 2$ mA		720		mV
Forward current transfer ratio	h_{FE}	$V_{CE} = 10$ V, $I_C = 2$ mA	100		250	—
Transition frequency *	f_T	$V_{CB} = 10$ V, $I_E = -15$ mA, f = 200 MHz		1 300		MHz
Power gain	G_P	$V_{CB} = 10$ V, $I_E = -1$ mA, f = 100 MHz		20		dB

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

*: Pulse measurement

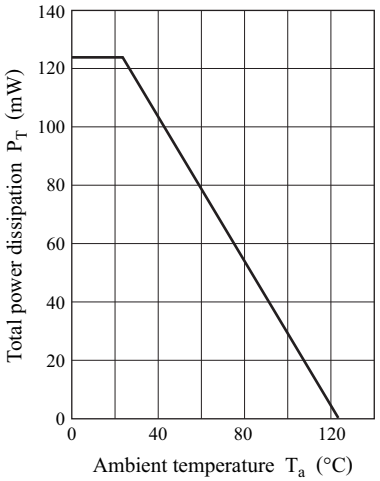
• CCD Load Device

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Pinchi off current	I_P	$V_{DS} = 8$ V, $V_G = 0$	5.0		7.0	mA
Output impedance	Z_O	$V_{DS} =$ V, $V_G = 0$		0.02		MΩ

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

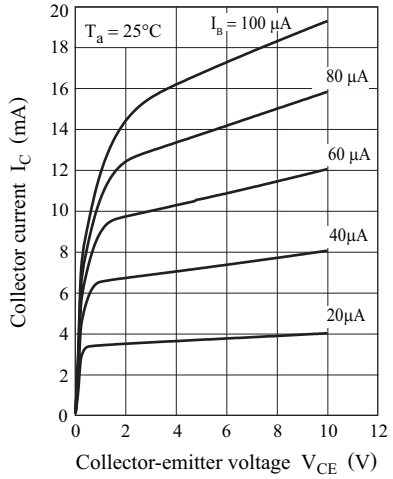
Common characteristics chart

P_T — T_a

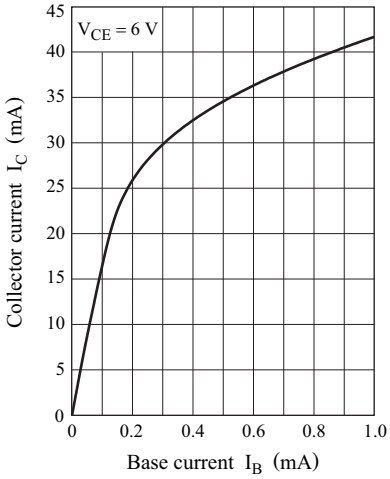


Characteristics charts of Tr

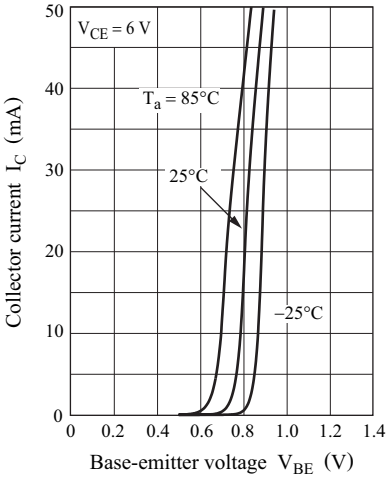
I_C — V_{CE}



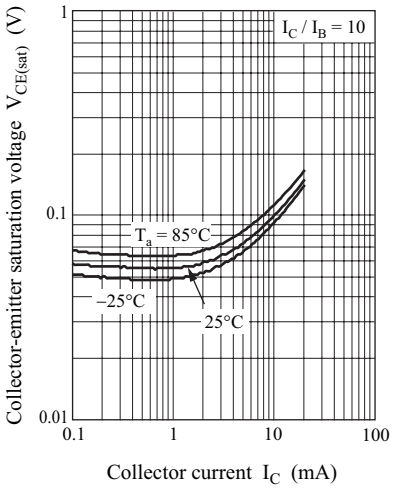
I_C — I_B



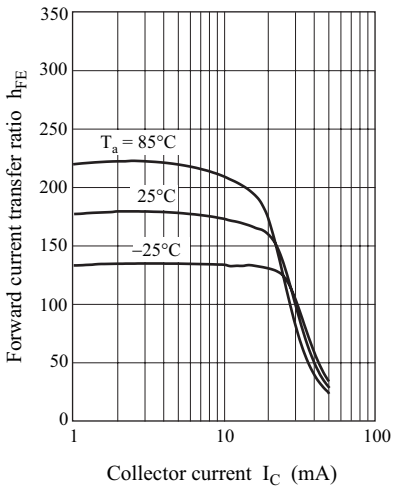
I_C — V_{BE}



$V_{CE(sat)}$ — I_C

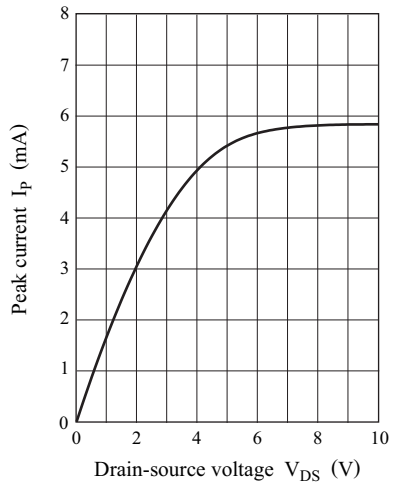


h_{FE} — I_C



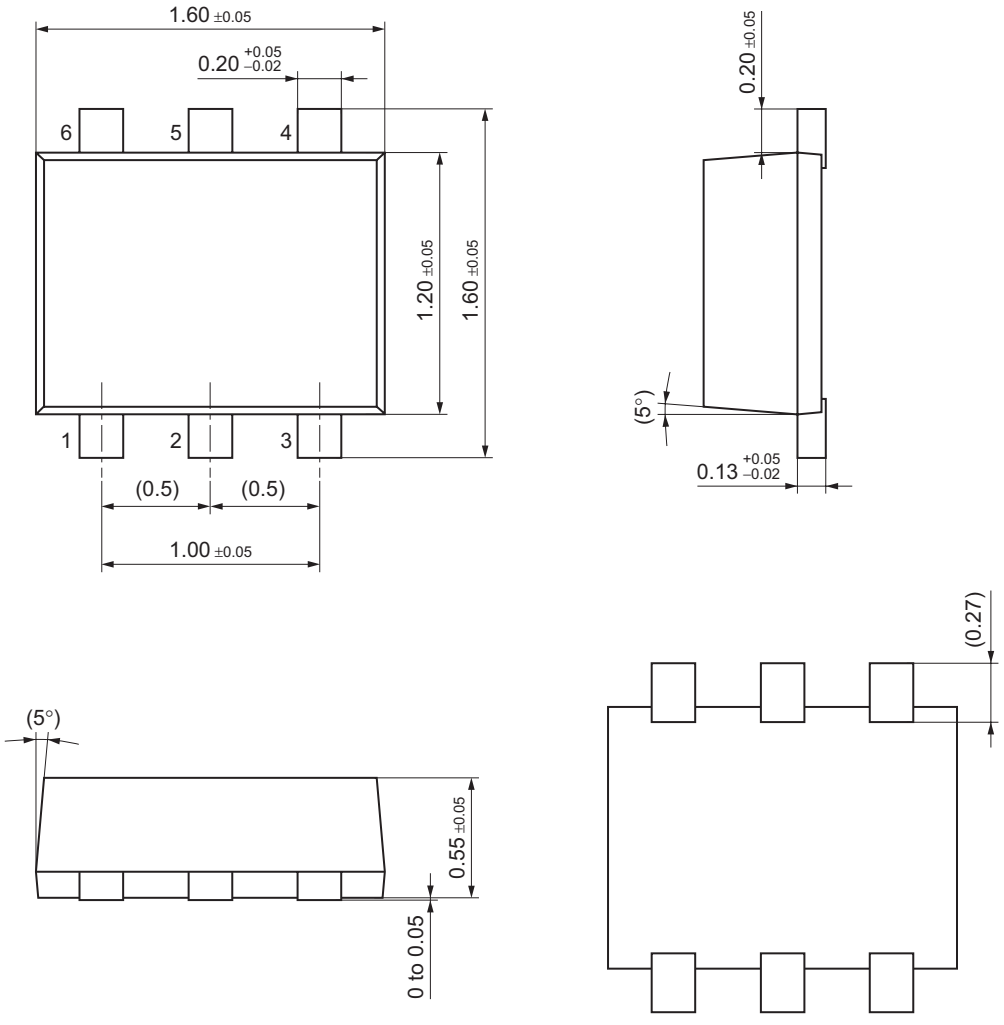
Characteristics charts of CCD load device

I_P — V_{DS}



SSMini6-F2

Unit: mm



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